

**Notice of References Cited**Application/Control No.  
09/836,449Applicant(s)/Patent Under  
Reexamination  
FONASH ET AL.Examiner  
Richard A. BoothArt Unit  
2812

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	M	US-			

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**NON-PATENT DOCUMENTS**

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	V	Tayanaka et al., "Thin-Film Crystalline Silicon Solar Cells Obtained by Separation of a Porous Silicon Sacrificial Layer", 2 <sup>nd</sup> World Conference and Exhibition on Photovoltaic Solar Energy Conversion, July 6, 1998, pages 1272-1277.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.